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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74HC245

Octal Bus Transceivers (with 3-state outputs)



ADE-205-475 (Z)

1st. Edition

Sep. 2000

Description

Each device has an active low enable input $\overline{G}$ and a direction control input, DIR. When DIR is high, data flows from the A inputs to the B outputs. When DIR is low, data flows from the B inputs to the A outputs. The HD74HC245 transfers true data from one bus to the other. This device does not have schmitt trigger inputs.

Features

- High Speed Operation: $t_{pd} = 8 \text{ ns typ (} C_L = 50 \text{ pF)}$
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: $1 \mu\text{A max}$
- Low Quiescent Supply Current: $I_{CC} \text{ (static)} = 4 \mu\text{A max (} T_a = 25^\circ\text{C)}$

Function Table

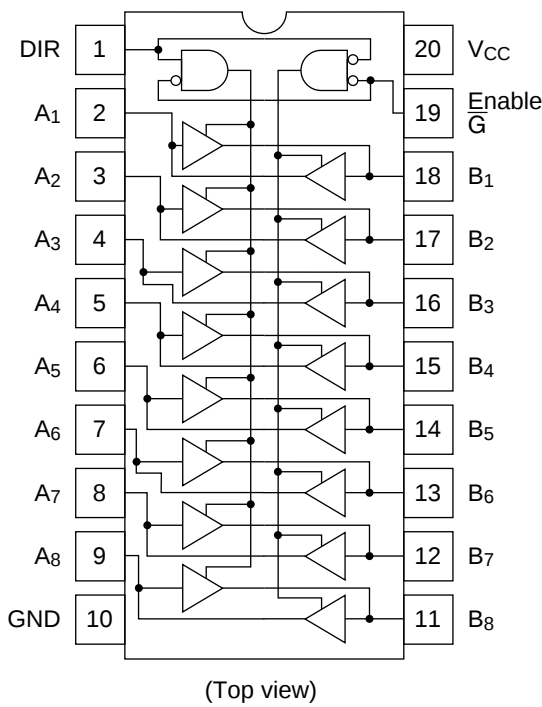
Enable G	Direction Control DIR	Operation
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

H : high level

L : low level

X : irrelevant

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to $V_{CC} + 0.5$	V
Output voltage	V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
DC current drain per pin	I_{OUT}	± 35	mA
DC current drain per V_{CC} , GND	I_{CC}, I_{GND}	± 75	mA
DC input diode current	I_{IK}	± 20	mA
DC output diode current	I_{OK}	± 20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	Tstg	-65 to +150	°C

DC Characteristics

Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V _{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V _{IH} or V _{IL} I _{OH} = -20 μA	
		4.5	4.4	4.5	—	4.4	—			
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—			I _{OH} = -6 mA
		6.0	5.68	—	—	5.63	—			I _{OH} = -7.8 mA
	V _{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V _{IH} or V _{IL} I _{OL} = 20 μA	
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I _{OL} = 6 mA
		6.0	—	—	0.26	—	0.33			I _{OL} = 7.8 mA
Off-state output current	I _{OZ}	6.0	—	—	±0.5	—	±5.0	μA	Vin = V _{IH} or V _{IL} , Vout = V _{CC} or GND	
Input current	I _{in}	6.0	—	—	±0.1	—	±1.0	μA	Vin = V _{CC} or GND	
Quiescent supply current	I _{CC}	6.0	—	—	4.0	—	40	μA	Vin = V _{CC} or GND, Iout = 0 μA	

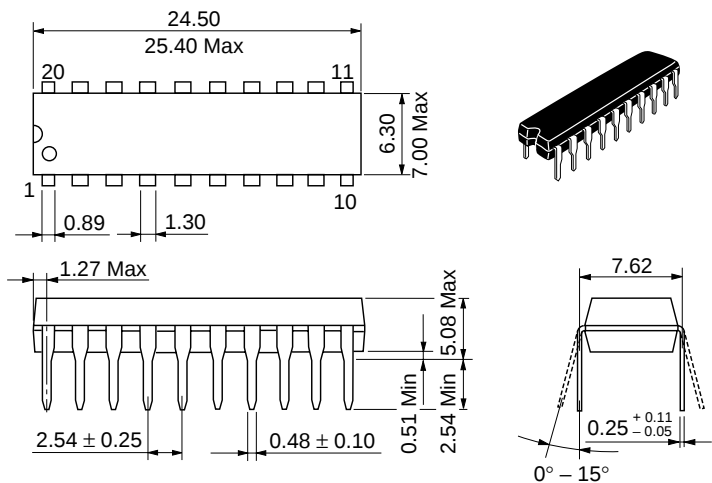
HD74HC245

AC Characteristics (C_L = 50 pF, Input t_r = t_f = 6 ns)

Item	Symbol	V _{CC} (V)	Ta = 25°C		Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min			Max
Propagation delay time	t _{PLH}	2.0	—	—	90	—	115	ns	
		4.5	—	8	18	—	23		
		6.0	—	—	15	—	20		
	t _{PHL}	2.0	—	—	90	—	115	ns	
		4.5	—	8	18	—	23		
		6.0	—	—	15	—	20		
Output enable time	t _{ZL}	2.0	—	—	150	—	190	ns	
		4.5	—	16	30	—	38		
		6.0	—	—	26	—	32		
	t _{ZH}	2.0	—	—	150	—	190	ns	
		4.5	—	12	30	—	38		
		6.0	—	—	26	—	32		
Output disable time	t _{LZ}	2.0	—	—	150	—	190	ns	
		4.5	—	17	30	—	38		
		6.0	—	—	26	—	32		
	t _{HZ}	2.0	—	—	150	—	190	ns	
		4.5	—	18	30	—	38		
		6.0	—	—	26	—	32		
Output rise/fall time	t _{TLH}	2.0	—	—	60	—	75	ns	
	t _{THL}	4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	C _{in}	—	—	5	10	—	10	pF	

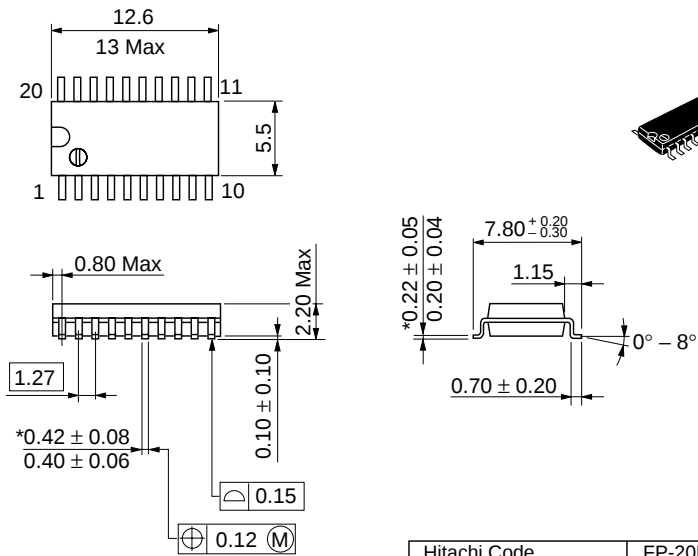
Package Dimensions

Unit: mm



Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.26 g

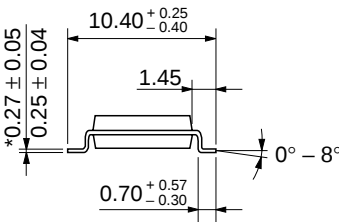
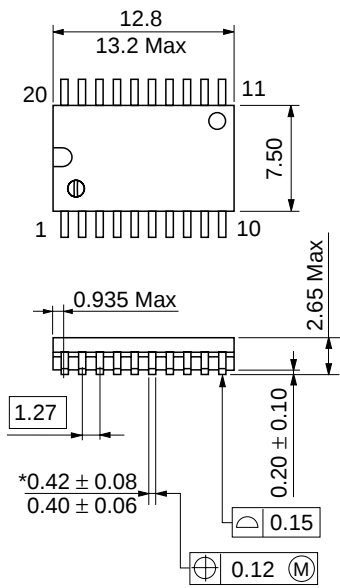
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.31 g

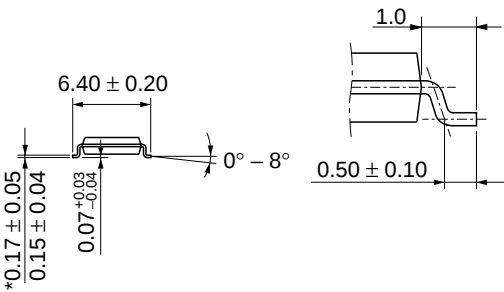
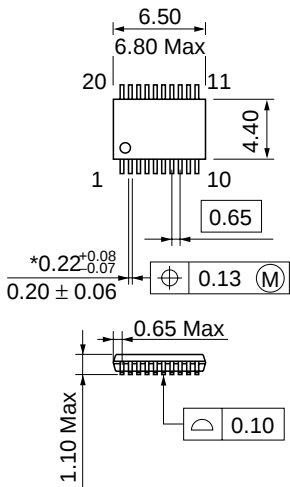
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Mass (reference value)	0.52 g

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-20DA
JEDEC	—
EIAJ	—
Mass (reference value)	0.07 g

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